



2811

Response  
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8/8/3  
Sunder

IN THE UNITED STATES  
PATENT AND TRADEMARK OFFICE

In re Patent Application of:

<b>Inventor:</b>	Chen, et al	<b>Confirmation No:</b>	1660
<b>Serial No.</b>	10/085,866	<b>Examiner:</b>	Hu, Shouxiang
<b>Filed:</b>	Feb 27, 2002	<b>Group Art Unit:</b>	2811
<b>Title:</b>	Emission Layer Formed By Rapid Thermal Formation Process		

Commissioner for Patents  
P O BOX 1450  
Alexandria VA 22313-1450

RESPONSE TO RESTRICTION REQUIREMENT

In response to your Office Action/Restriction Requirement dated July 1, 2003;  
Applicants affirm the election of Group II, (Claims 13-19) without traverse.

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Respectfully submitted,  
  
Chen, et al

By: Timothy F. Myers  
Timothy F. Myers, Reg No: 42,919  
Attorney For Applicants

I hereby certify that this correspondence is being deposited on the date indicated below with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, PO Box 1450, Alexandria, VA 22313.

Timothy F. Myers  
Signature  
Timothy F. Myers  
Typed Name  
7/23/03  
Date of Signature

10013802

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re U.S. Patent Application

Applicant: Chen et al.

Serial No.: 10/085866

Filing Date: Feb 27 2002

For: EMISSION LAYER FORMED BY  
RAPID THERMAL FORMATION  
PROCESS

Art Unit: Unassigned



#4 per Annot-A  
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PRELIMINARY AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

Prior to consideration and calculating the fees for the above-referenced  
Application, please amend the Application as follows:

In the Specification:

Please replace the paragraph beginning on page 3, line <sup>30</sup>~~20~~, with the  
following rewritten paragraph:

A<sup>1</sup> Referring now to FIG. 1, a preferred embodiment emitter 10 of the  
invention is shown in a two-dimensional schematic cross section. The preferred  
embodiment emitter 10 is a metal-insulator-semiconductor (MIS) device including a flat